

MOSFET – N-Channel QFET

1000 V, 8 A, 1.45 Ω

FQD30N06

Description

This N-Channel Enhancement Mode Power MOSFET is produced using onsemi's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

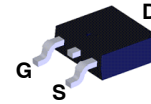
Features

- 22.7 A, 60 V $R_{DS(on)} = 45 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 11.4 \text{ A}$
- Low Gate Charge (Typ. 19 nC)
- Low C_{rss} (Typ. 40 pF)
- 100% Avalanche Tested
- This Device is Pb-Free Halide, Free and RoHS Compliant

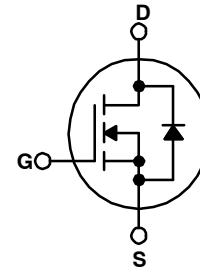
MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

| Symbol | Parameter | Value | Unit |
|----------------|--|-------------|---------------------|
| V_{DSS} | Drain to Source Voltage | 60 | V |
| I_D | Drain Current | | A |
| | - Continuous ($T_C = 25^\circ\text{C}$) | 22.7 | |
| | - Continuous ($T_C = 100^\circ\text{C}$) | 14.3 | |
| I_{DM} | Drain Current – Pulsed (Note 1) | 90.8 | A |
| V_{GSS} | Gate–Source Voltage | ± 25 | V |
| E_{AS} | Single Pulse Avalanche Energy (Note 2) | 280 | mJ |
| I_{AR} | Avalanche Current (Note 1) | 22.7 | A |
| E_{AR} | Repetitive Avalanche Energy (Note 1) | 4.4 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 7.0 | V/ns |
| P_D | Power Dissipation ($T_A = 25^\circ\text{C}$) * | 2.5 | W |
| | Power Dissipation | | W |
| | - ($T_C = 25^\circ\text{C}$) | 44 | |
| | - Derate Above 25°C | 0.35 | W/ $^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +150 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | 300 | $^\circ\text{C}$ |

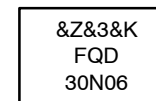
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



TO-252-3
CASE 369AS



MARKING DIAGRAM



&Z = Assembly Plant Code
&3 = Numeric Date Code
&K = 2-Digit Lot Code
FQD30N06 = Specific Device Code

ORDERING INFORMATION

| Device | Package | Shipping† |
|----------|-----------------------|-----------------------|
| FQD30N06 | TO-252-3 (Pb-Free) | 2500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

FQD30N06

THERMAL CHARACTERISTICS

| Symbol | Parameter | Value | Unit |
|-----------------|---|-------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 2.85 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max. | 110 | |
| | Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max. | 50 | |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|----|------|------|------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 60 | – | – | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$, Referenced to 25°C | – | 0.06 | – | V/°C |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$ | – | – | 1 | μA |
| | Zero Gate Voltage Drain Current | $V_{DS} = 48\text{ V}, T_C = 125^\circ\text{C}$ | – | – | 10 | μA |
| I_{GSSF} | Gate to Body Leakage Current, Forward | $V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$ | – | – | 100 | nA |
| I_{GSSR} | Gate to Body Leakage Current, Reverse | $V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$ | – | – | -100 | nA |

On Characteristics

| | | | | | | |
|--------------|-----------------------------------|---|-----|-------|-------|---|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 2.0 | – | 4.0 | V |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10\text{ V}, I_D = 11.4\text{ A}$ | – | 0.036 | 0.045 | Ω |
| g_{FS} | Forward Transconductance | $V_{DS} = 25\text{ V}, I_D = 11.4\text{ A}$ | – | 15 | – | S |

Dynamic Characteristics

| | | | | | | |
|------------|------------------------------|---|---|-----|-----|----|
| C_{iss} | Input Capacitance | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$ | – | 725 | 945 | pF |
| C_{oss} | Output Capacitance | | – | 270 | 350 | pF |
| C_{riss} | Reverse Transfer Capacitance | | – | 40 | 52 | pF |

Switching Characteristics

| | | | | | | |
|--------------|---------------------|--|---|-----|-----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 30\text{ V}, I_D = 15\text{ A}, R_G = 25\ \Omega$ (Note 4) | – | 10 | 30 | ns |
| t_r | Turn-On Rise Time | | – | 85 | 180 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | – | 35 | 80 | ns |
| t_f | Turn-Off Fall Time | | – | 40 | 90 | ns |
| Q_g | Total Gate Charge | $V_{DS} = 48\text{ V}, I_D = 30\text{ A}, V_{GS} = 10\text{ V}$ (Note 4) | – | 19 | 25 | nC |
| Q_{gs} | Gate-Source Charge | | – | 5.4 | – | nC |
| Q_{gd} | Gate-Drain Charge | | – | 8.5 | – | nC |

Drain-Source Diode Characteristics and Maximum Ratings

| | | | | | | |
|----------|---|--|---|------|-----|----|
| I_S | Maximum Continuous Drain-Source Diode Forward Current | – | – | 22.7 | A | |
| I_{SM} | Maximum Pulsed Drain-Source Diode Forward Current | – | – | 90.8 | A | |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 22.7\text{ A}$ | – | – | 1.5 | V |
| t_{rr} | Reverse Recovery Time | $V_{GS} = 0\text{ V}, I_S = 30\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$ | – | 45 | – | ns |
| Q_{rr} | Reverse Recovery Charge | | – | 65 | – | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. Repetitive Rating: Pulse-width limited by maximum junction temperature.
2. $L = 630\ \mu\text{H}, I_{AS} = 227\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\ \Omega$ starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 30\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

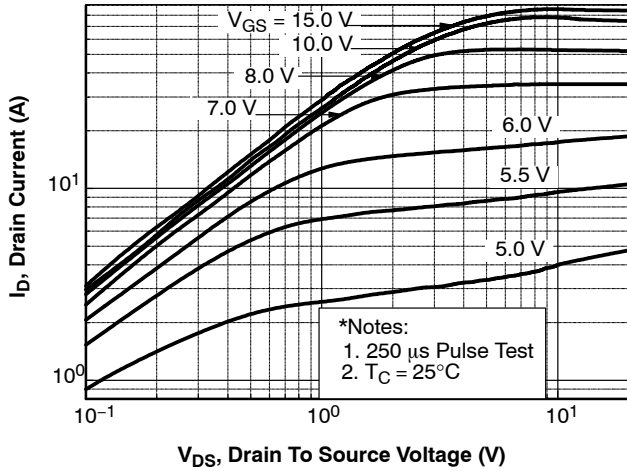


Figure 1. On-Region Characteristics

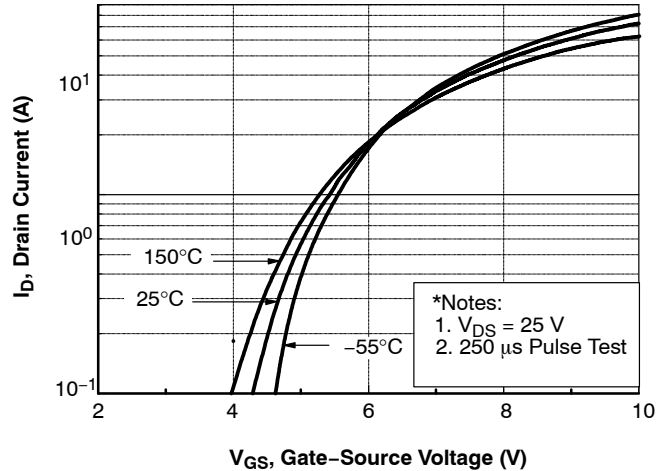


Figure 2. Transfer Characteristics

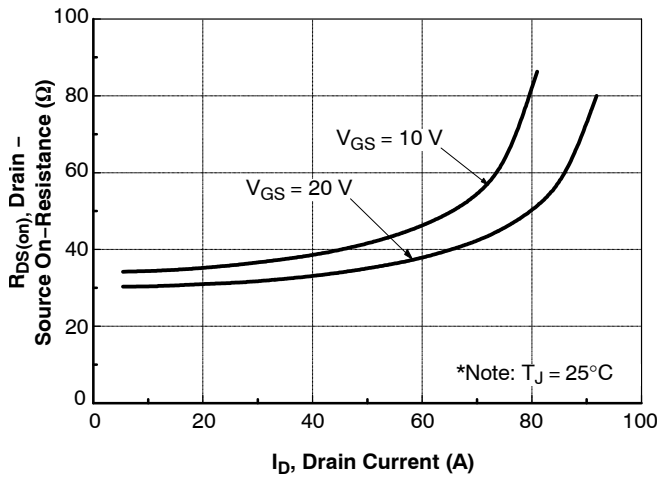


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

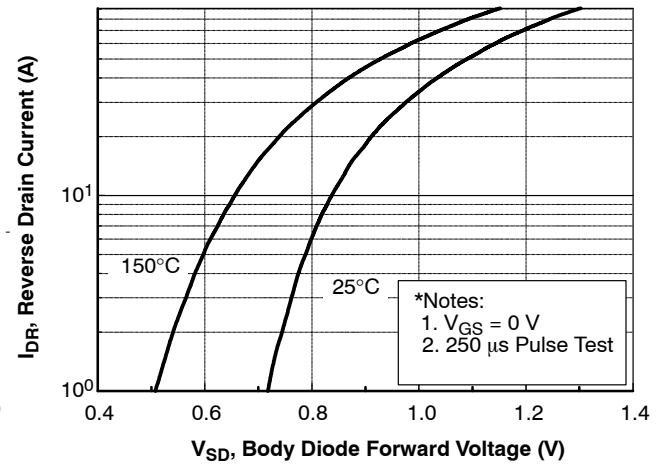


Figure 4. Body Diode Forward Voltage Variation vs Source Current and Temperature

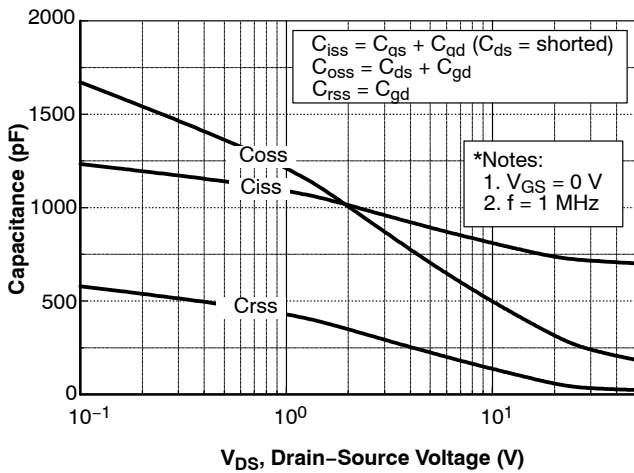


Figure 5. Capacitance Characteristics

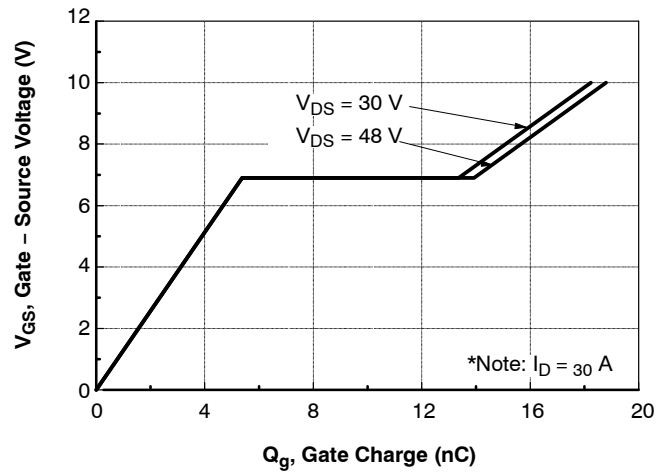


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS (CONTINUED)

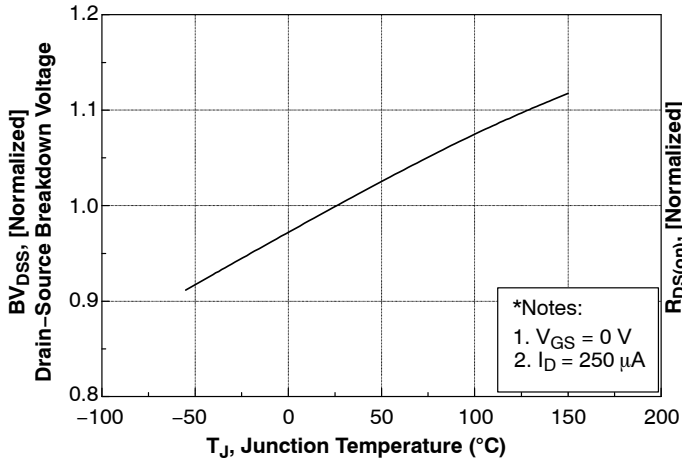


Figure 7. Breakdown Voltage Variation vs Temperature

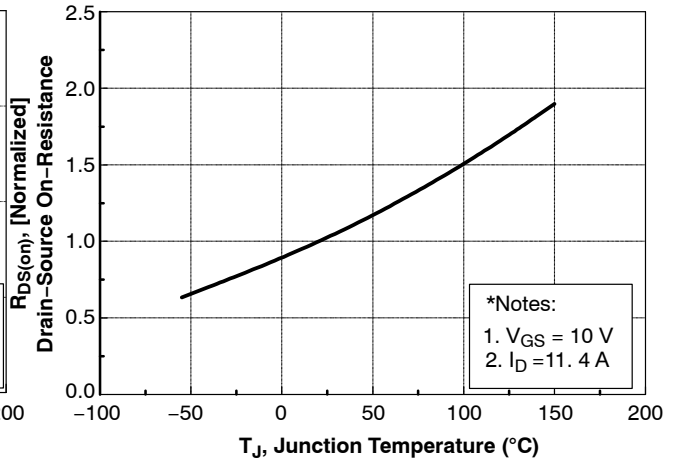


Figure 8. On-Resistance Variation vs Temperature

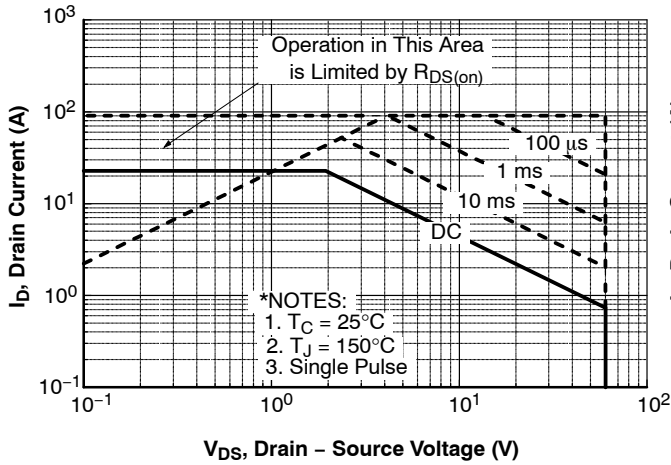


Figure 9. Maximum Safe Operating Area

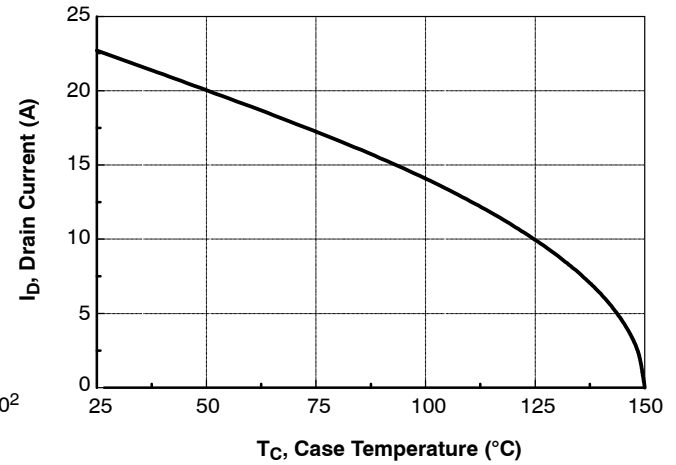


Figure 10. Maximum Drain Current vs. Case Temperature

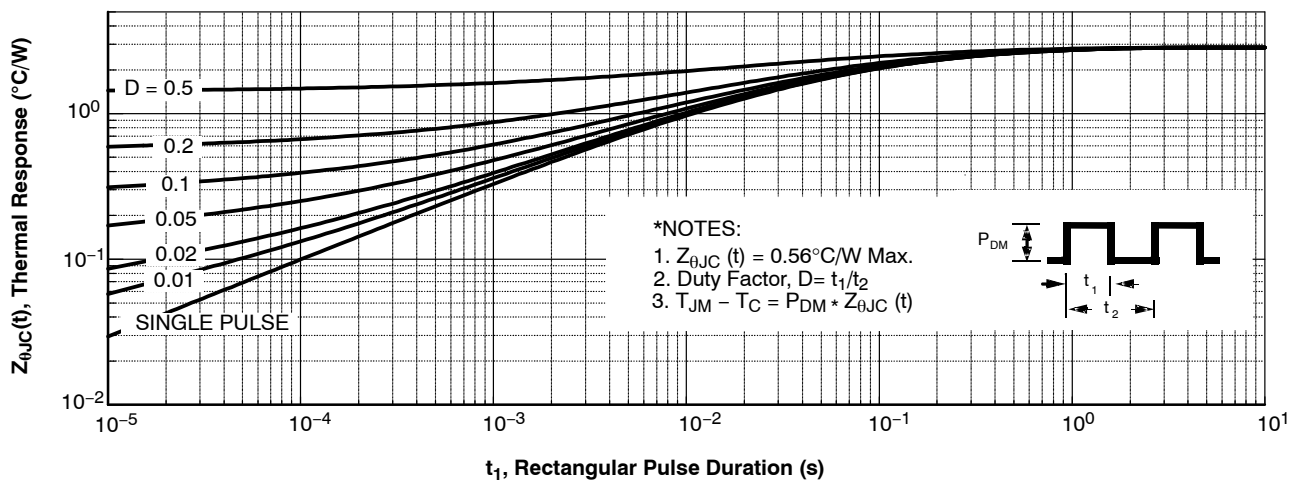


Figure 11. Transient Thermal Response Curve

FQD30N06

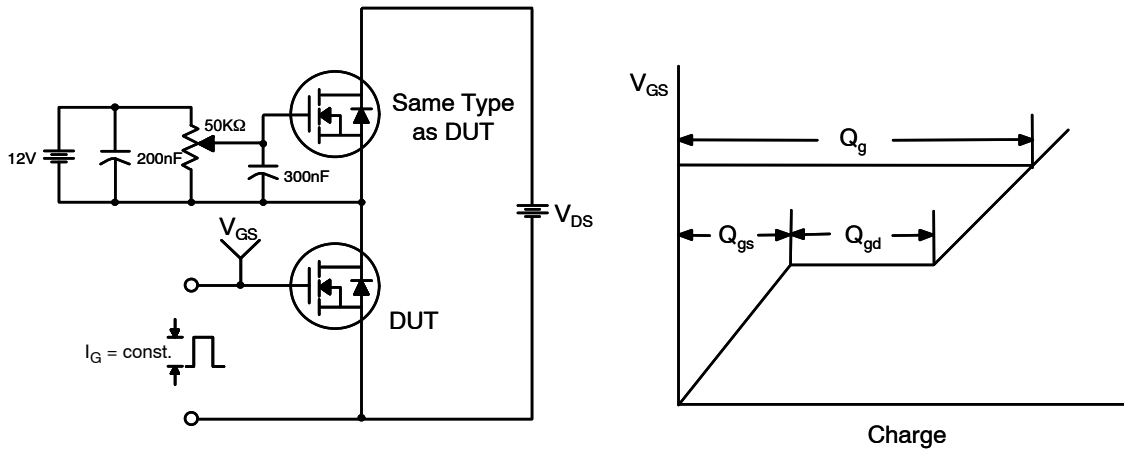


Figure 12. Gate Charge Test Circuit & Waveform

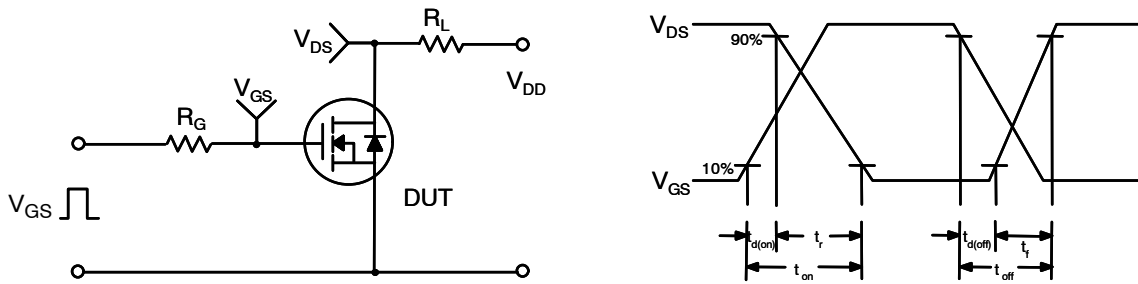


Figure 13. Resistive Switching Test Circuit & Waveforms

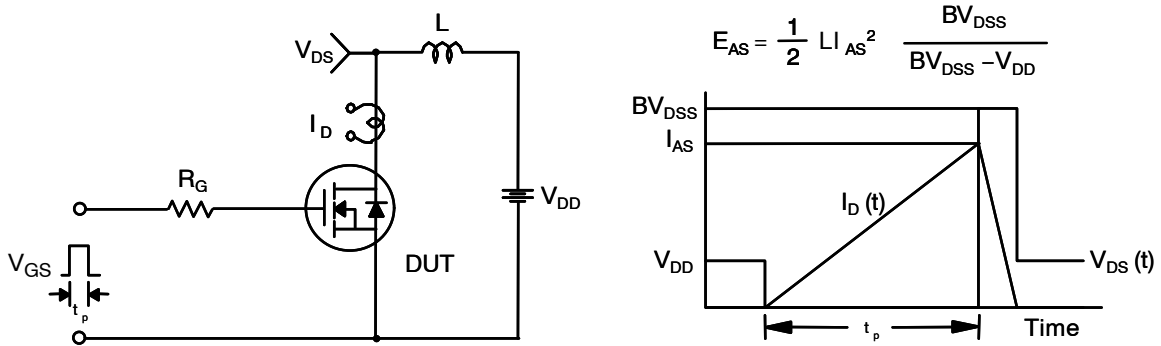


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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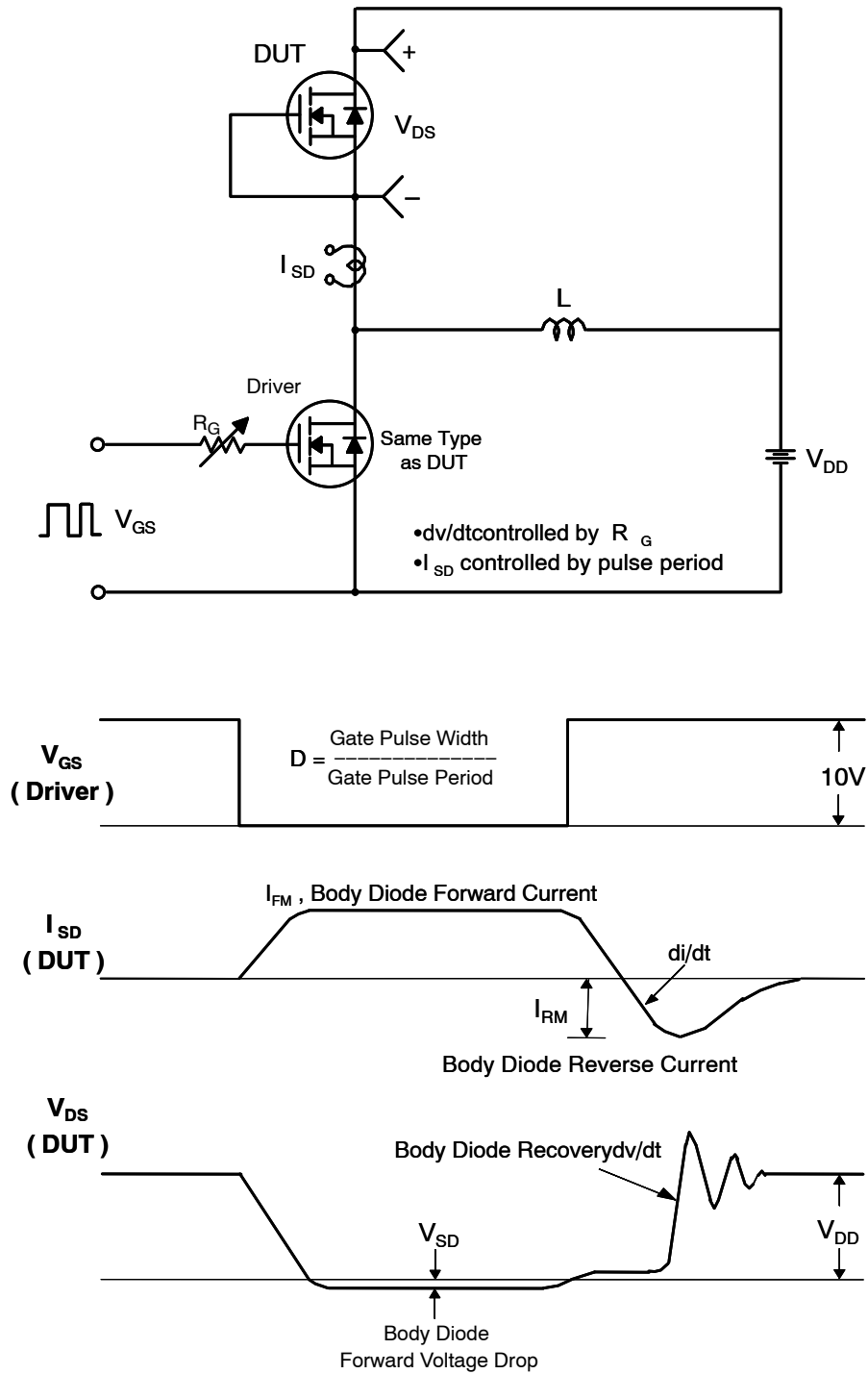
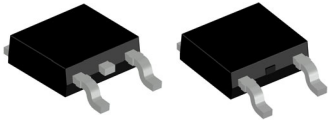
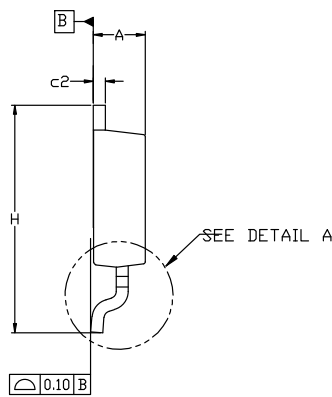
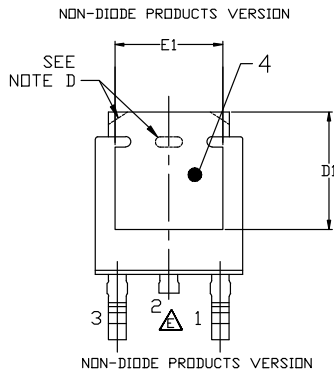
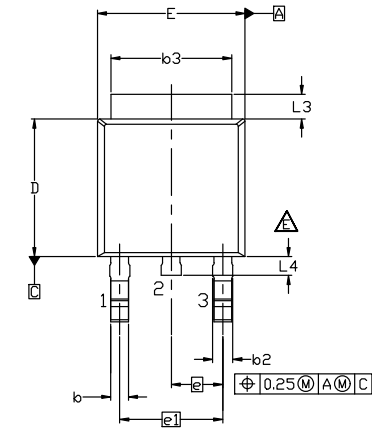


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

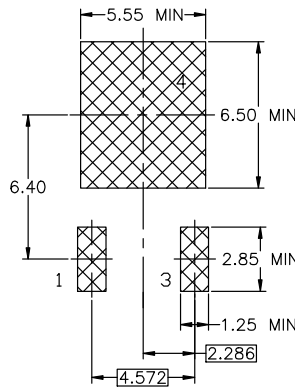
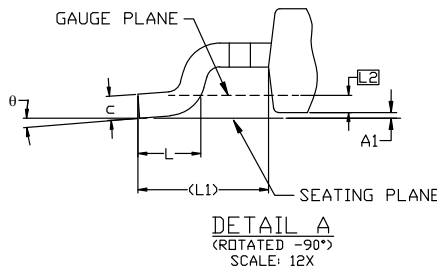


**DPAK3 6.10x6.54x2.29, 4.57P
CASE 369AS
ISSUE B**

DATE 20 DEC 2023



- NOTES: UNLESS OTHERWISE SPECIFIED
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2018.
 D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
 E) FOR DIODE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY STUB WITHOUT CENTER LEAD.
 F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TD228P991X239-3N.



LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

| DIM | MILLIMETERS | | |
|-------|-------------|------|-------|
| | MIN. | NOM. | MAX. |
| A | 2.18 | 2.29 | 2.39 |
| A1 | 0.00 | - | 0.127 |
| b | 0.64 | 0.77 | 0.89 |
| b2 | 0.76 | 0.95 | 1.14 |
| b3 | 5.21 | 5.34 | 5.46 |
| c | 0.45 | 0.53 | 0.61 |
| c2 | 0.45 | 0.52 | 0.58 |
| D | 5.97 | 6.10 | 6.22 |
| D1 | 5.21 | --- | --- |
| E | 6.35 | 6.54 | 6.73 |
| E1 | 4.32 | --- | --- |
| e | 2.286 BSC | | |
| e1 | 4.572 BSC | | |
| H | 9.40 | 9.91 | 10.41 |
| L | 1.40 | 1.59 | 1.78 |
| L1 | 2.90 REF | | |
| L2 | 0.51 BSC | | |
| L3 | 0.89 | 1.08 | 1.27 |
| L4 | --- | --- | 1.02 |
| theta | 0° | --- | 10° |

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

| | | |
|-------------------------|------------------------------------|--|
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